Lonten N-channel 40V, 110A, 5.0mΩ Power MOSFET

Description

These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and with stand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

Features

- 40V,110A,$R_{DS(ON).max}$=5.0mΩ@V_{GS}=10V
- Improved dv/dt capability
- Fast switching
- 100% EAS Guaranteed
- Green device available

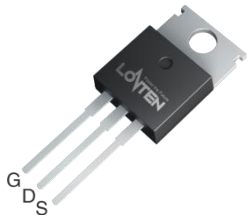
Applications

- Motor Drives
- UPS
- DC-DC Converter

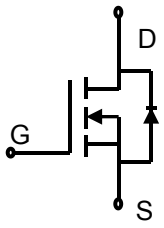
Product Summary

V_{DSS}	40V
$R_{DS(on).max}$@ V_{GS}=10V	5.0mΩ
I_D	110A

Pin Configuration



TO-220



N-Channel MOSFET

Absolute Maximum Ratings

T_C = 25°C unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	40	V
Continuous drain current (T_C = 25°C)	I_D	110	A
Continuous drain current (T_C = 100°C)		71	A
Pulsed drain current[1)]	I_{DM}	440	A
Gate-Source voltage	V_{GSS}	±20	V
Avalanche energy[2)]	E_{AS}	156	mJ
Power Dissipation (T_C = 25°C)	P_D	106	W
Storage Temperature Range	T_{STG}	-55 to +150	°C
Operating Junction Temperature Range	T_J	-55 to +150	°C

Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	1.17	°C/W

Package Marking and Ordering Information

Device	Device Package	Marking
LNC04R050	TO-220	LNC04R050

Electrical Characteristics

T_J = 25°C unless otherwise noted

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static characteristics						
Drain-source breakdown voltage	BV_{DSS}	V_{GS}=0 V, I_D=250uA	40	---	---	V
Gate threshold voltage	$V_{GS(th)}$	V_{DS}=V_{GS}, I_D=250uA	1.0	---	2.0	V
Drain-source leakage current	I_{DSS}	V_{DS}=40 V, V_{GS}=0 V, T_J = 25°C	---	---	1	μA
		V_{DS}=32 V, V_{GS}=0 V, T_J = 125°C	---	---	30	μA
Gate leakage current, Forward	I_{GSSF}	V_{GS}=20 V, V_{DS}=0 V	---	---	100	nA
Gate leakage current, Reverse	I_{GSSR}	V_{GS}=-20 V, V_{DS}=0 V	---	---	-100	nA
Drain-source on-state resistance	$R_{DS(on)}$	V_{GS}=10 V, I_D=40 A	---	3.8	5	mΩ
		V_{GS}=4.5 V, I_D=30 A	---	4.7	6.2	mΩ
Forward transconductance	g_{fs}	V_{DS} =5 V , I_D=30 A	---	79	---	S
Dynamic characteristics						
Input capacitance	C_{iss}	V_{DS} = 20 V, V_{GS} = 0 V, F = 1MHz	---	4023.6	---	pF
Output capacitance	C_{oss}		---	410.4	---	
Reverse transfer capacitance	C_{rss}		---	338.5	---	
Turn-on delay time	$t_{d(on)}$	V_{DD} = 30V,V_{GS}=15V, I_D =30 A	---	231.6	---	ns
Rise time	t_r		---	213.6	---	
Turn-off delay time	$t_{d(off)}$		---	219.2	---	
Fall time	t_f		---	74	---	
Gate resistance	R_g	V_{GS}=0V, V_{DS}=0V, F=1MHz	---	2.4	---	Ω
Gate charge characteristics						
Gate to source charge	Q_{gs}	V_{DS}=30 V, I_D=30A, V_{GS}=10V	---	11	---	nC
Gate to drain charge	Q_{gd}		---	16.7	---	
Gate charge total	Q_g		---	66.7	---	
Drain-Source diode characteristics and Maximum Ratings						
Continuous Source Current	I_S		---	---	110	A
Pulsed Source Current[3)]	I_{SM}		---	---	440	A
Diode Forward Voltage	V_{SD}	V_{GS}=0V, I_S=40A, T_J=25℃	---	---	1.2	V
Reverse Recovery Time	t_{rr}	I_S=20A,di/dt=100A/us, T_J=25℃	---	41.4	---	ns
Reverse Recovery Charge	Q_{rr}		---	29	---	nC

Notes:

1: Repetitive Rating: Pulse width limited by maximum junction temperature.

2: V_{DD}=20V, V_{GS}=10V, L=0.5mH, I_{AS}=25A, R_G=25Ω, Starting T_J=25℃.

3: Pulse Test：Pulse Width ≤300μs, Duty Cycle≤2%.

Electrical Characteristics Diagrams

Figure 1. Typ. Output Characteristics

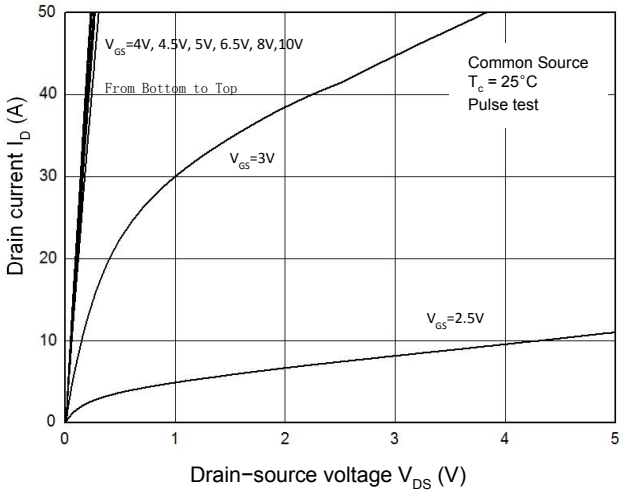


Figure 2. Transfer Characteristics

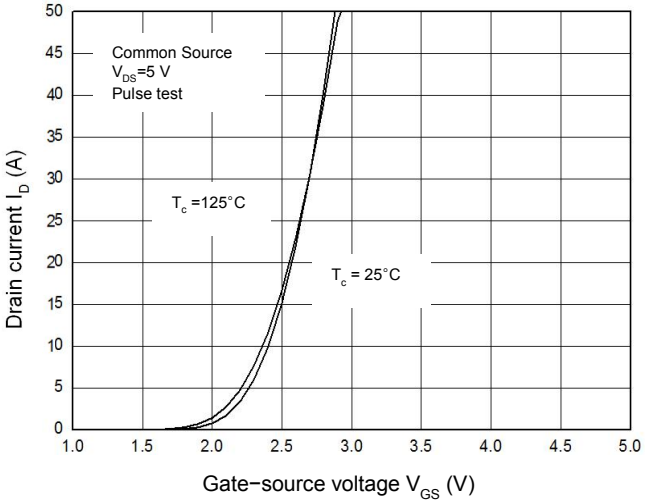


Figure 3. Capacitance Characteristics

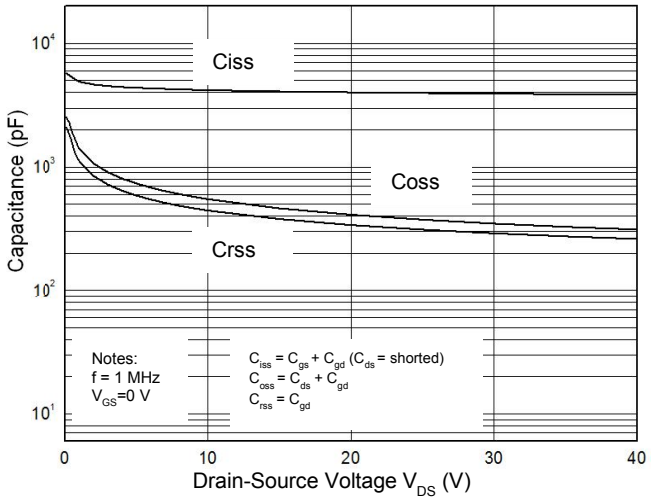


Figure 4. Gate Charge Waveform

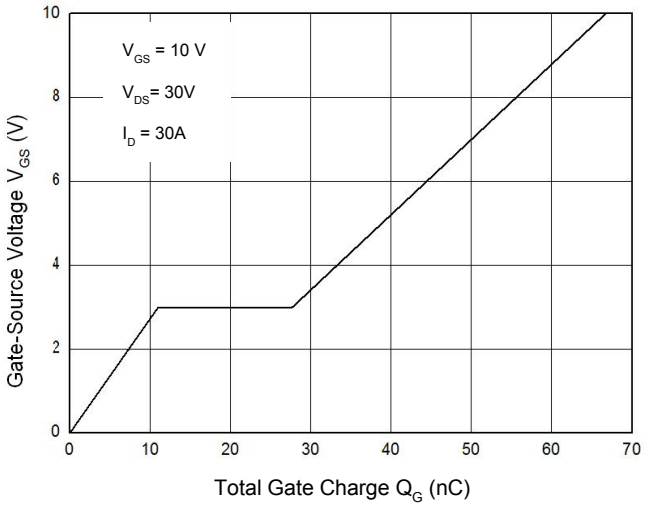


Figure 5. Body-Diode Characteristics

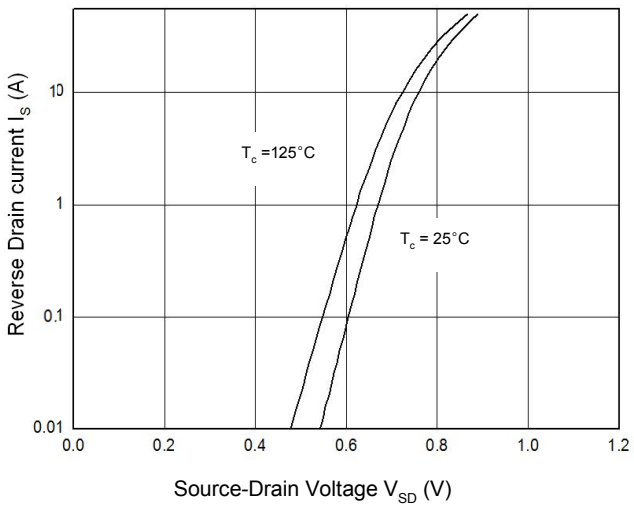


Figure 6. Rdson-Drain Current

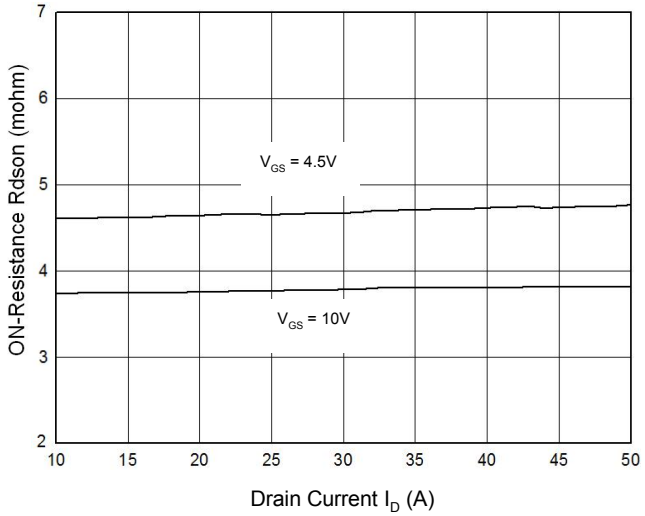


Figure 7. Rdson-Junction Temperature(℃)

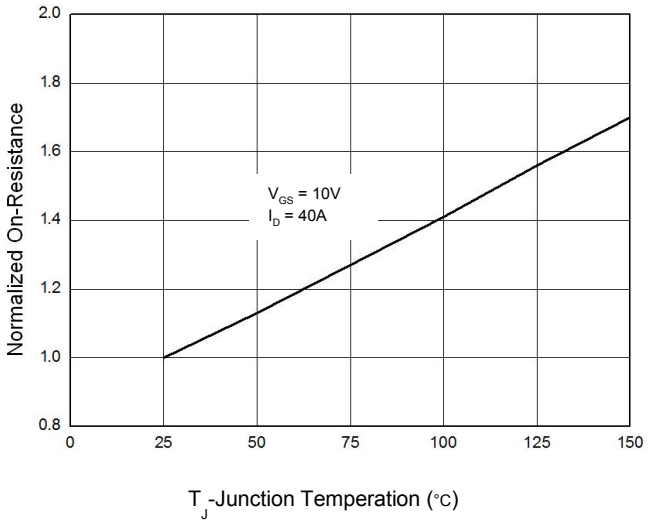


Figure 8. Maximum Safe Operating Area

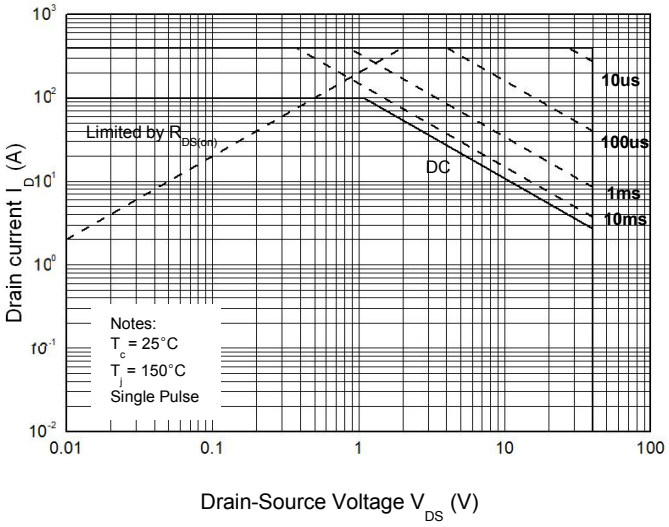
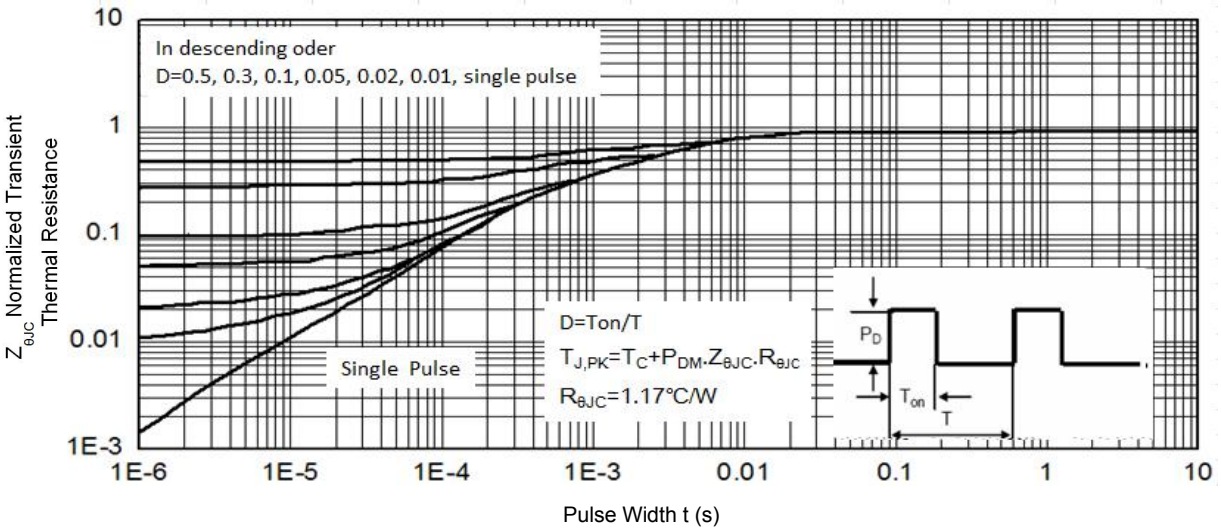


Figure 9. Normalized Maximum Transient Thermal Impedance (RthJC)



Test Circuit & Waveform

Figure 8. Gate Charge Test Circuit & Waveform

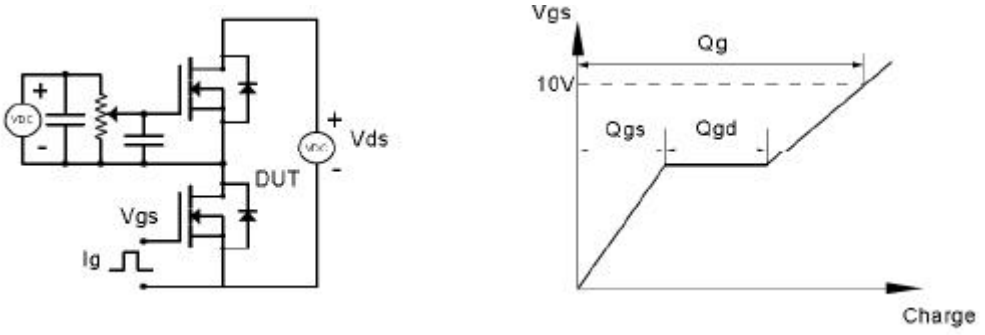


Figure 9. Resistive Switching Test Circuit & Waveforms

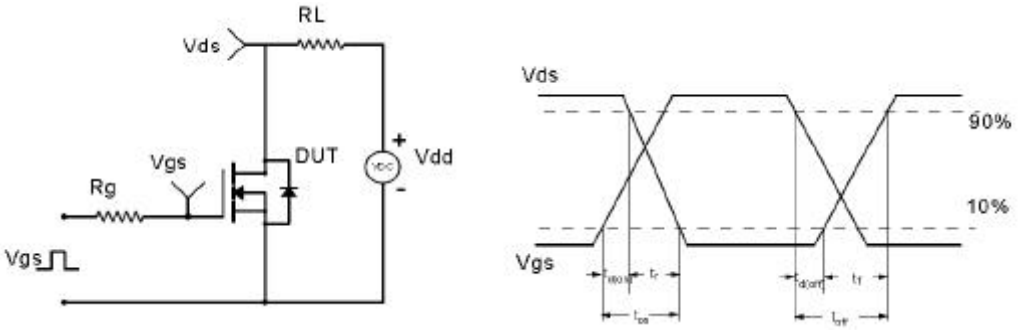


Figure 10. Unclamped Inductive Switching (UIS) Test Circuit & Waveform

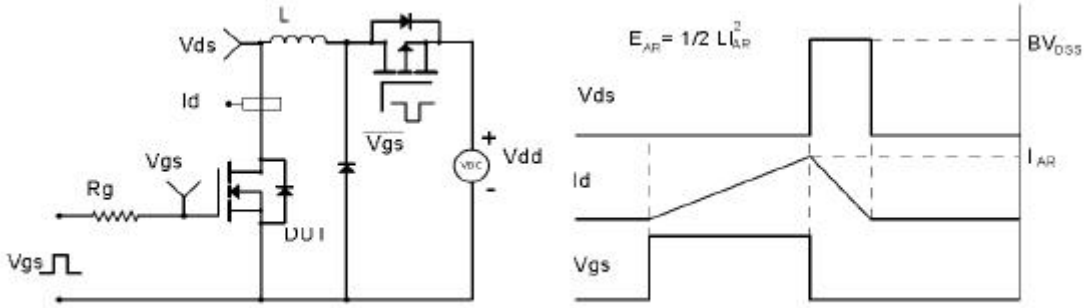
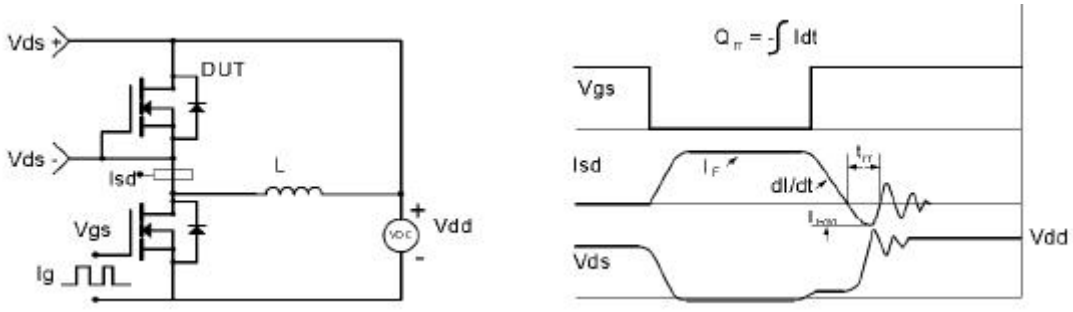
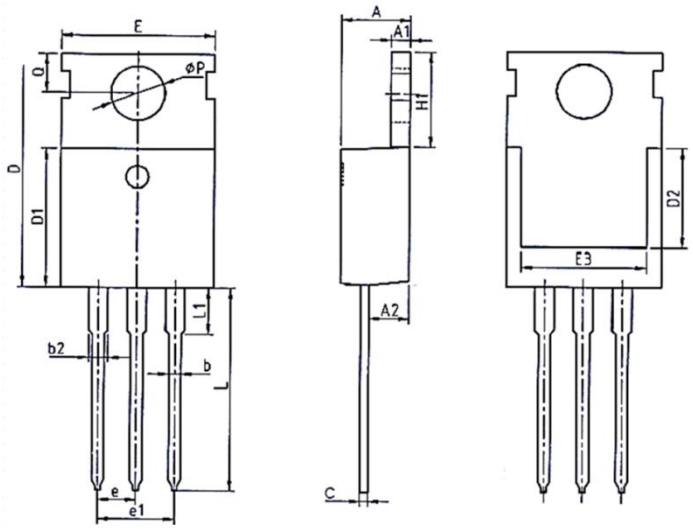


Figure 11. Diode Recovery Circuit & Waveform

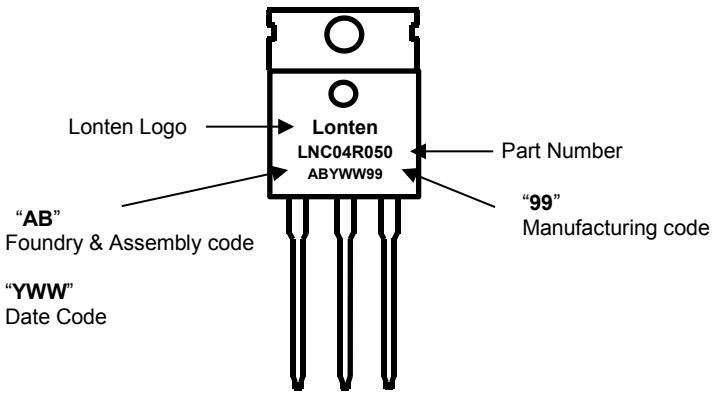


TO-220 PACKAGE INFORMATION



COMMON DIMENSIONS						
SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX
A	4.37	4.57	4.70	0.172	0.180	0.185
A1	1.25	1.30	1.40	0.049	0.051	0.055
A2	2.20	2.40	2.60	0.087	0.094	0.102
b	0.70	0.80	0.95	0.028	0.031	0.037
b2	1.17	1.27	1.47	0.046	0.050	0.058
c	0.45	0.50	0.60	0.018	0.020	0.024
D	15.10	15.60	16.10	0.594	0.614	0.634
D1	8.80	9.10	9.40	0.346	0.358	0.370
D2	5.50	-	-	0.217	-	-
E	9.70	10.00	10.30	0.382	0.394	0.406
E3	7.00	-	-	0.276	-	-
e	2.54BCS			0.1BSC		
e1	5.08BCS			0.2REF		
H1	6.25	6.50	6.85	0.246	0.256	0.270
L	12.75	13.50	13.80	0.502	0.531	0.543
L1	-	3.10	3.40	-	0.122	0.134
ØP	3.40	3.60	3.80	0.134	0.142	0.150
Q	2.60	2.80	3.00	0.102	0.110	0.118

TO-220 Part Marking Information



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